

L Number	Hits	Search Text	DB	Time stamp
-	39	((("5015502") or ("5648113") or ("5654035") or ("6037003") or ("6319730") or ("6278166") or ("6406960") or ("6420279") or ("6407435") or ("5120672") or ("6008091") or ("6171900") or ("6309927") or ("6438030") or ("6461905") or ("6573197") or ("5907766") or ("6451657") or ("6451641") or ("6407435")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 08:53
-	129	composite near3 dielectric and (high-K high?k (high near2 K))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 07:16
-	825	(257/310).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 18:16
-	327	(438/441,746,760).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 18:16
-	129	composite near3 dielectric and (high-K high?k (high near2 K))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 07:16
-	142	composite near3 dielectric and (high-K high?k (high near2 K))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 07:16
-	1944	((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 08:55
-	521	((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))) and ((silicon near2 dioxide) (silicon near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 08:58
-	474	((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))) and ((silicon near2 dioxide) (silicon near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and ((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide) (barium near2 oxide) (titanium near2 oxide) PMN PST PZN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 09:02
-	42	((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))) and ((silicon near2 dioxide) (silicon near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and ((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide) (barium near2 oxide) (titanium near2 oxide) PMN PST PZN)) and MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 09:28
-	0	((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))) and ((silicon near2 dioxide) (silicon near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and ((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide) (barium near2 oxide) (titanium near2 oxide) PMN PST PZN)) and ((gate near3 dielectric) same (FET EEPROM SONOS))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 09:30
-	0	((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))) and ((silicon near2 dioxide) (silicon near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and ((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide) (barium near2 oxide) (titanium near2 oxide) PMN PST PZN)) and (gate near3 dielectric) and (FET EEPROM SONOS MOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 09:30

-	28	((((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))) and ((silicon near2 dioxide) (silicon near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and ((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide) (barium near2 oxide) (titanium near2 oxide) PMN PST PZN)) and (gate near3 dielectric) and (FET EEPROM SONOS MOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 09:30
-	13	((((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))) and ((silicon near2 dioxide) (silicon near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and ((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide) (barium near2 oxide) (titanium near2 oxide) PMN PST PZN)) and ((gate near3 dielectric) same (FET EEPROM SONOS))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 10:41
-	4	((("6013553") or ("6020243")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 10:16
-	10016	(257/411,412,382-410,368).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 10:47
-	3937	(438/300,305,216,261,421,591,595).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 10:48
-	0	10/656470	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 10:48
-	2	10/051790	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 10:56
-	8	2002/0106536	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 10:57
-	8	2002/0106536	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 11:01
-	0	(2002/0106536).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 10:58
-	2	"20020106536"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 11:03
-	2	"20020190311"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 11:04

-	2	"20020115252"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 11:10
-	2	"20020142624"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 11:10